

ON Semiconductor

Is Now



To learn more about onsemi™, please visit our website at
www.onsemi.com

onsemi and onsemi. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

NTD50N03R

Power MOSFET

25 V, 45 A, Single N-Channel, DPAK

Features

- Planar Technology
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- Pb-Free Packages are Available

Applications

- VCORE DC-DC Buck Converter Applications
- Optimized for High Side Switching

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	25	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current ($R_{\theta JA}$) (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	9.2	A
		$T_A = 85^{\circ}\text{C}$		7.2	
Power Dissipation ($R_{\theta JA}$) (Note 1)		$T_A = 25^{\circ}\text{C}$	P_D	2.1	W
Continuous Drain Current ($R_{\theta JA}$) (Note 2)		$T_A = 25^{\circ}\text{C}$	I_D	7.8	A
		$T_A = 85^{\circ}\text{C}$		6.0	
Power Dissipation ($R_{\theta JA}$) (Note 2)		$T_A = 25^{\circ}\text{C}$	P_D	1.5	W
Continuous Drain Current ($R_{\theta JC}$) (Note 1)		$T_C = 25^{\circ}\text{C}$	I_D	45	A
		$T_C = 85^{\circ}\text{C}$		35	
Power Dissipation ($R_{\theta JC}$) (Note 1)		$T_C = 25^{\circ}\text{C}$	P_D	50	W
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 10\text{ }\mu\text{s}$		I_{DM}	180	A
Current Limited by Package	$T_A = 25^{\circ}\text{C}$		$I_{DmaxPkg}$	45	A
Operating Junction and Storage Temperature			T_J, T_{stg}	-55 to 175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	45	A
Drain-to-Source (dv/dt)			dv/dt	8.0	V/ns
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^{\circ}\text{C}$, $V_{DD} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_L = 6.32\text{ A}_{pk}$, $L = 1.0\text{ mH}$, $R_G = 25\text{ }\Omega$)			E_{AS}	20	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 sq in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

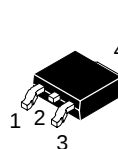
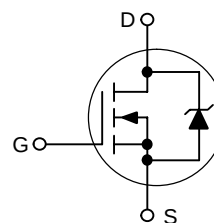


ON Semiconductor®

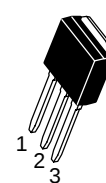
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
25 V	12.5 m Ω @ 10 V	45 A
	19 m Ω @ 4.5 V	

N-Channel



CASE 369AA
DPAK
(Surface Mount)
STYLE 2

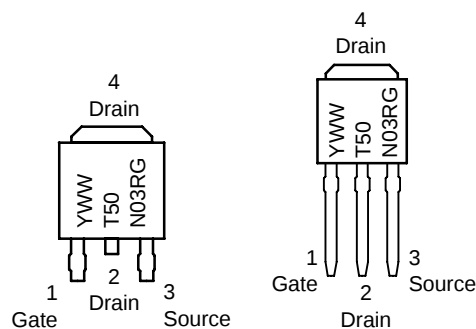


CASE 369D
DPAK
(Straight Lead)
STYLE 2



CASE 369AC
3 IPAK
(Straight Lead)

MARKING DIAGRAMS & PIN ASSIGNMENTS



Y = Year
WW = Work Week
T50N03R = Device Code
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

NTD50N03R

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	3.0	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	71.4	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	100	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	25			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			-16		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 20\text{ V}$	$T_J = 25^\circ\text{C}$		1.5	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.0	1.7	2.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-5.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 11.5\text{ V}$	$I_D = 30\text{ A}$		12	m Ω
			$I_D = 15\text{ A}$		11.7	
		$V_{GS} = 10\text{ V}$	$I_D = 30\text{ A}$		12.5	
			$I_D = 15\text{ A}$		14	
		$V_{GS} = 4.5\text{ V}$	$I_D = 30\text{ A}$		21	
			$I_D = 15\text{ A}$		19	
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		15		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 12\text{ V}$		610	750	pF
Output Capacitance	C_{oss}			300		
Reverse Transfer Capacitance	C_{rss}			125		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		6.0	10	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.9		
Gate-to-Source Charge	Q_{GS}			1.9		
Gate-to-Drain Charge	Q_{GD}			3.7		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		15		nC
Threshold Gate Charge	$Q_{G(TH)}$			1.0		
Gate-to-Source Charge	Q_{GS}			1.9		
Gate-to-Drain Charge	Q_{GD}			3.9		

- Surface-mounted on FR4 board using 1 sq in pad, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.
- Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.

NTD50N03R

ELECTRICAL CHARACTERISTICS (continued) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
-----------	--------	----------------	-----	-----	-----	------

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 30\text{ A}, R_G = 3.0\ \Omega$		8.2		ns
Rise Time	t_r			9.6		
Turn-Off Delay Time	$t_{d(off)}$			11.2		
Fall Time	t_f			6.8		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 30\text{ A}, R_G = 3.0\ \Omega$		5.0		ns
Rise Time	t_r			84		
Turn-Off Delay Time	$t_{d(off)}$			15		
Fall Time	t_f			4.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 30 A	T _J = 25°C		0.85	1.1	V
			T _J = 125°C		0.71		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 30 A			24		ns
Charge Time	t _a				14		
Discharge Time	t _b				10.5		
Reverse Recovery Charge	Q _{RR}					14	

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_a = 25^\circ\text{C}$		2.49		nH
Drain Inductance	L_D			0.02		
Gate Inductance	L_G			3.46		
Gate Resistance	R_G			3.75		Ω

6. Switching characteristics are independent of operating junction temperatures.

NTD50N03R

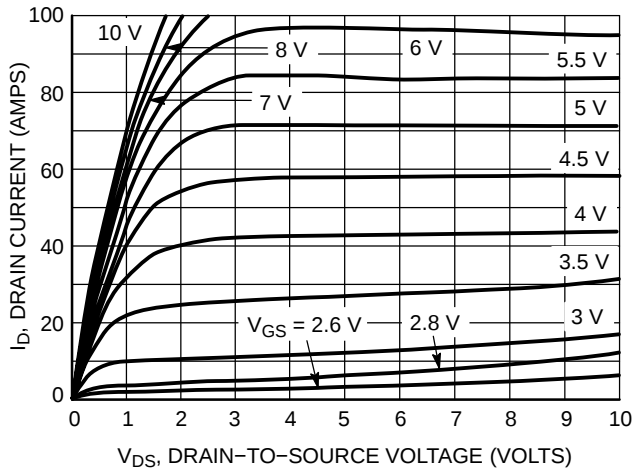


Figure 1. On-Region Characteristics

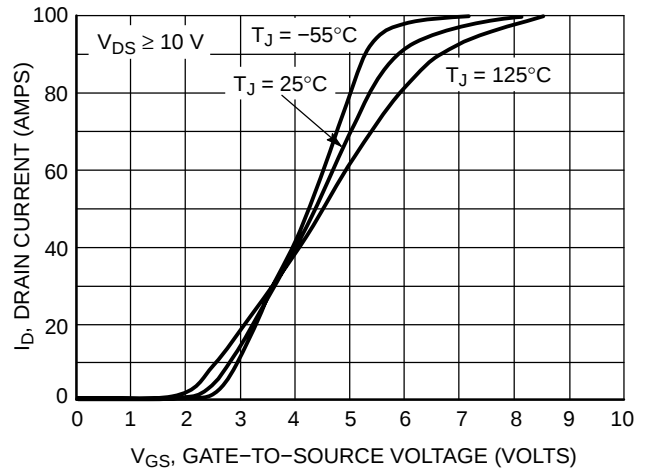


Figure 2. Transfer Characteristics

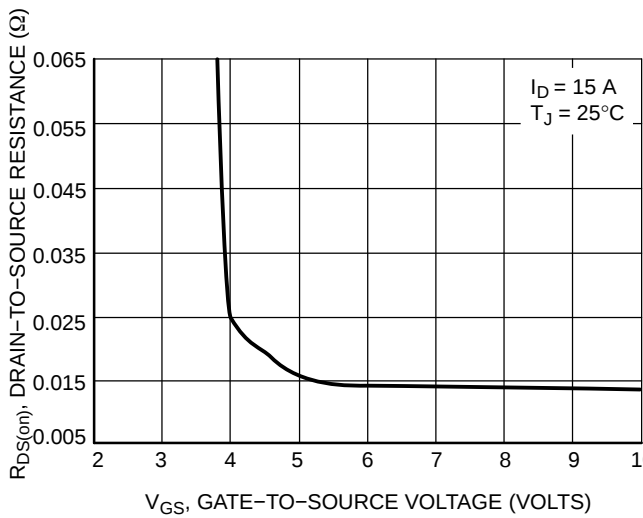


Figure 3. On-Resistance versus Gate-to-Source Voltage

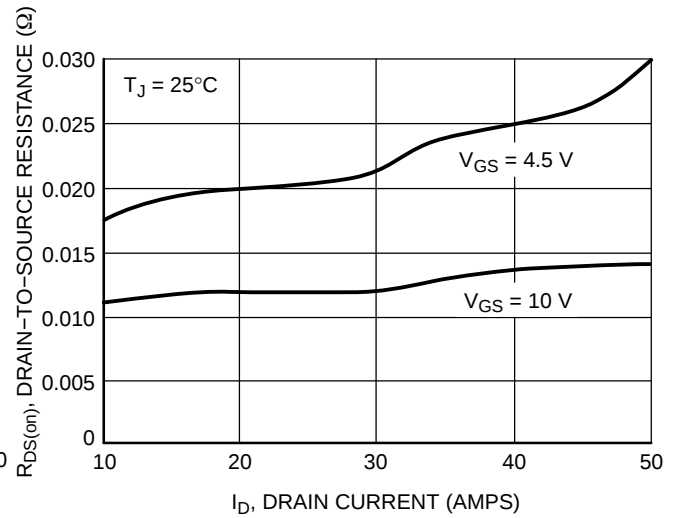


Figure 4. On-Resistance versus Drain Current and Gate Voltage

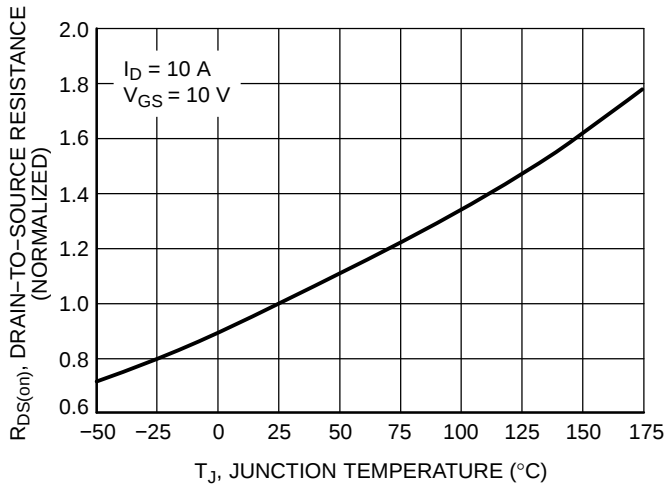


Figure 5. On-Resistance Variation with Temperature

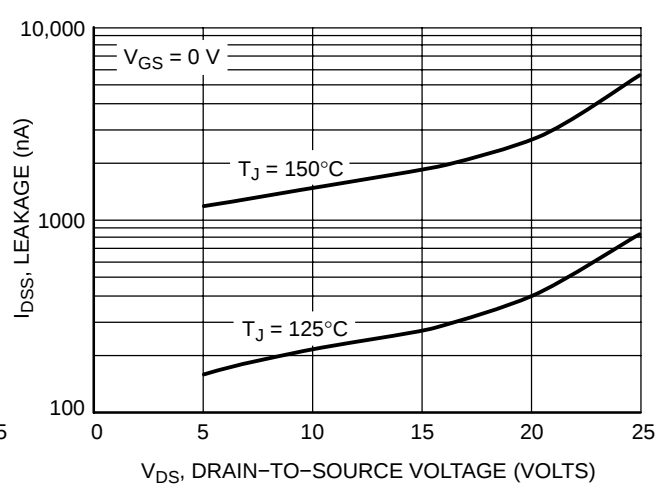


Figure 6. Drain-to-Source Leakage Current versus Voltage

NTD50N03R

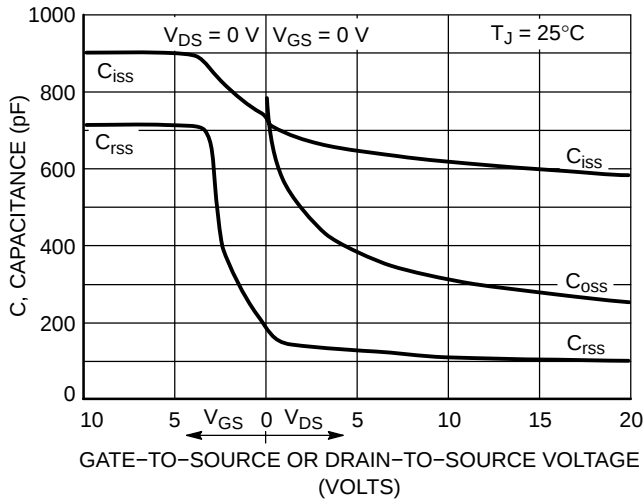


Figure 7. Capacitance Variation

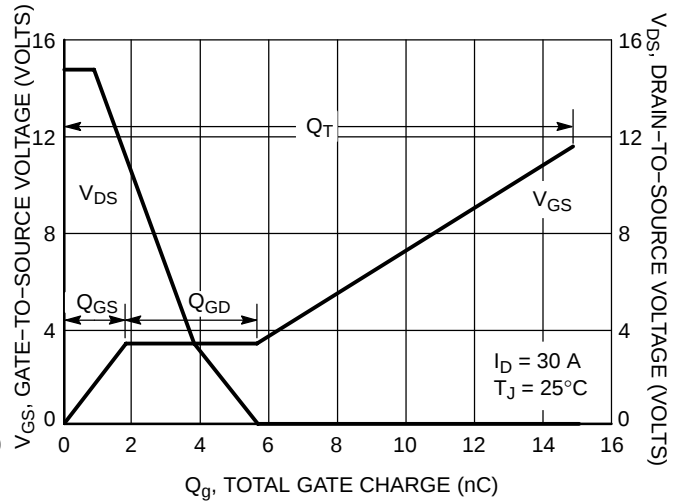


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

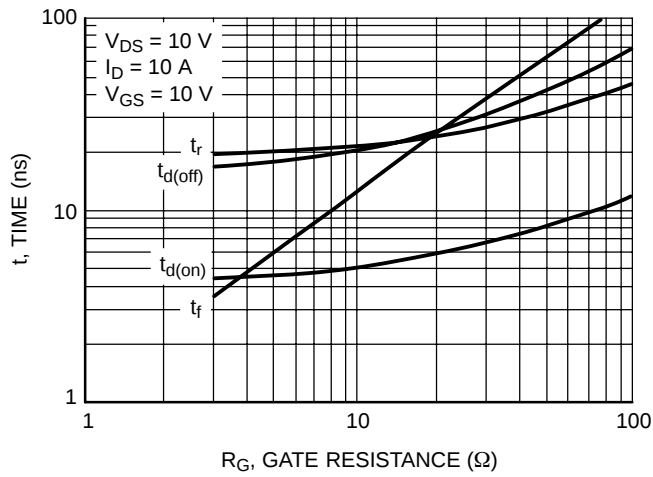


Figure 9. Resistive Switching Time Variation versus Gate Resistance

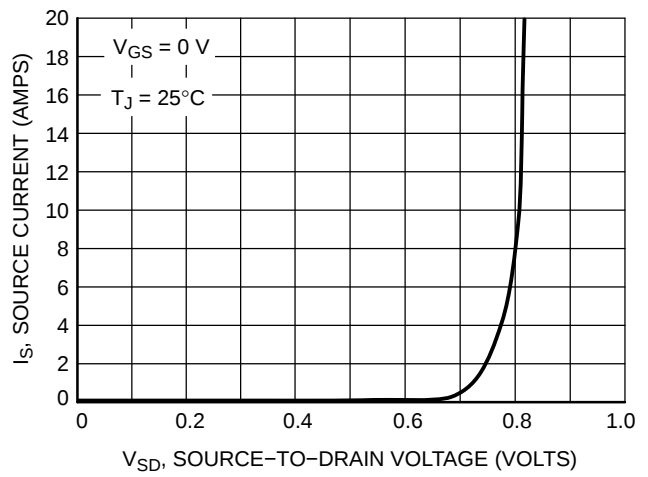


Figure 10. Diode Forward Voltage versus Current

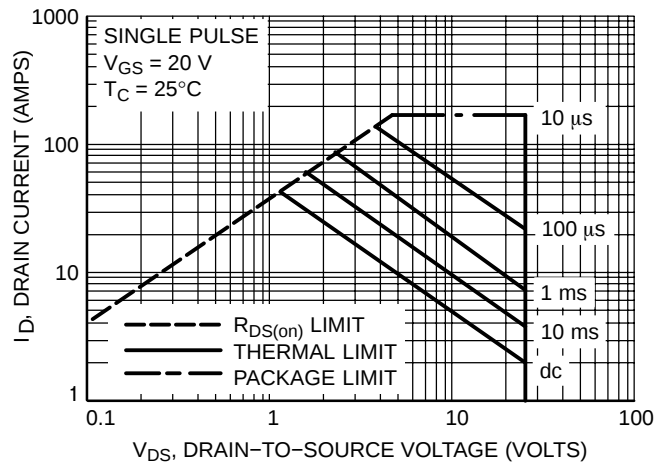


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTD50N03R

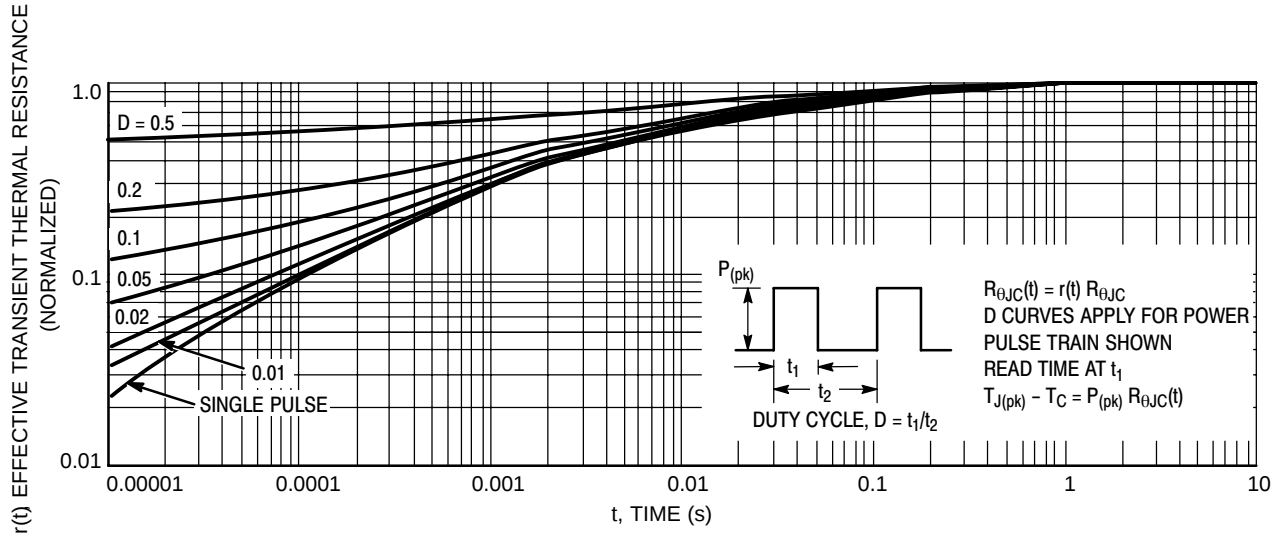


Figure 12. Thermal Response

ORDERING INFORMATION

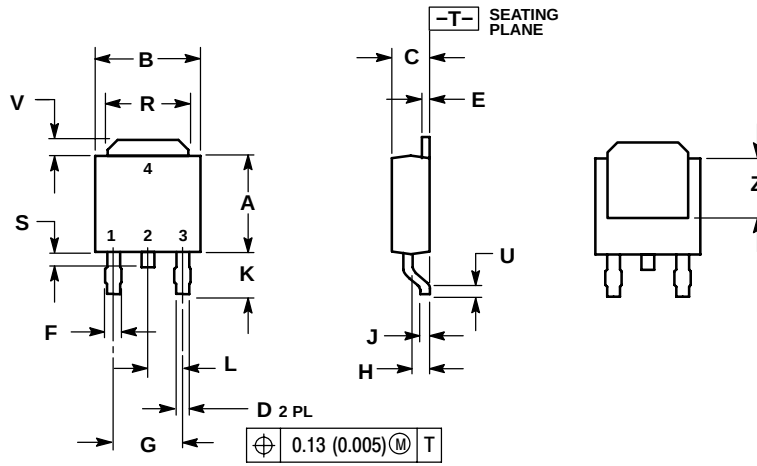
Order Number	Package	Shipping [†]
NTD50N03R	DPAK-3	75 Units / Rail
NTD50N03RG	DPAK-3 (Pb-Free)	75 Units / Rail
NTD50N03RT4	DPAK-3	2500 / Tape & Reel
NTD50N03RT4G	DPAK-3 (Pb-Free)	2500 / Tape & Reel
NTD50N03R-1	DPAK-3 Straight Lead	75 Units / Rail
NTD50N03R-1G	DPAK-3 Straight Lead (Pb-Free)	75 Units / Rail
NTD50N03R-35	DPAK-3 Straight Lead Trimmed (3.5 ± 0.15 mm)	75 Units / Rail
NTD50N03R-35G	DPAK-3 Straight Lead Trimmed (3.5 ± 0.15 mm) (Pb-Free)	75 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTD50N03R

PACKAGE DIMENSIONS

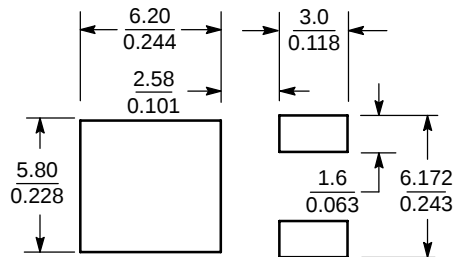
DPAK CASE 369C-01 ISSUE O



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

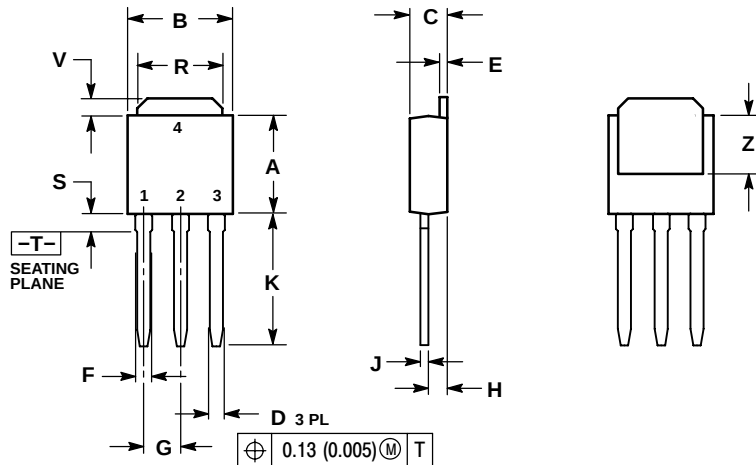
SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}} \right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DPAK CASE 369D-01 ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

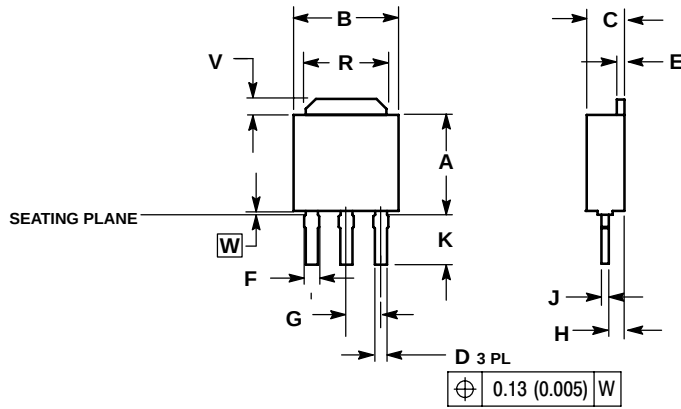
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
- PIN 1. GATE
 - DRAIN
 - SOURCE
 - DRAIN

NTD50N03R

PACKAGE DIMENSIONS

3 IPAK, STRAIGHT LEAD CASE 369AC-01 ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. SEATING PLANE IS ON TOP OF DAMBAR POSITION.
4. DIMENSION A DOES NOT INCLUDE DAMBAR POSITION OR MOLD GATE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.043	0.94	1.09
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.134	0.142	3.40	3.60
R	0.180	0.215	4.57	5.46
V	0.035	0.050	0.89	1.27
W	0.000	0.010	0.000	0.25

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your
local Sales Representative.

NTD50N03R/D